

FQP13N50CF / FQPF13N50CF 500V N-Channel MOSFET

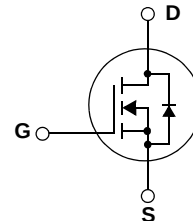
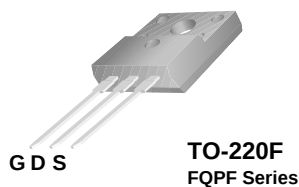
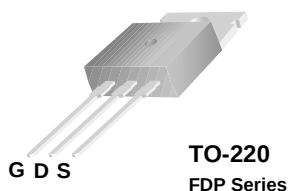
Features

- 13A, 500V, $R_{DS(on)} = 0.54\Omega$ @ $V_{GS} = 10V$
- Low gate charge (typical 43 nC)
- Low C_{rss} (typical 20pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability
- Fast recovery body diode (typical 100ns)

Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficient switched mode power supplies and active power factor correction.



Absolute Maximum Ratings

Symbol	Parameter	FQP13N50CF	FQPF13N50CF	Unit
V_{DSS}	Drain-Source Voltage	500		V
I_D	Drain Current - Continuous ($T_C = 25^\circ\text{C}$)	13	13*	A
	- Continuous ($T_C = 100^\circ\text{C}$)	8	8*	A
I_{DM}	Drain Current - Pulsed (Note 1)	52	52*	A
V_{GSS}	Gate-Source voltage	± 30		V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	530		mJ
I_{AR}	Avalanche Current (Note 1)	13		A
E_{AR}	Repetitive Avalanche Energy (Note 1)	19.5		mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.5		V/ns
P_D	Power Dissipation ($T_C = 25^\circ\text{C}$)	195	48	W
	- Derate above 25°C	1.56	0.39	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150		$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds	300		$^\circ\text{C}$

*Drain current limited by maximum junction temperature

Thermal Characteristics

Symbol	Parameter	FQP13N50CF	FQPF13N50CF	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	0.64	2.58	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62.5	62.5	$^\circ\text{C/W}$

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FQP13N50CF	FQP13N50CF	TO-220	-	-	50
FQPF13N50CF	FQPF13N50CF	TO-220F	-	-	50

Electrical Characteristics T_C = 25°C unless otherwise noted

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = 250μA, T _J = 25°C	500	--	--	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250μA, Referenced to 25°C	--	0.5	--	V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 500V, V _{GS} = 0V	--	--	10	μA
		V _{DS} = 400V, T _C = 125°C	--	--	100	μA
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30V, V _{DS} = 0V	--	--	100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30V, V _{DS} = 0V	--	--	-100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	2.0	--	4.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10V, I _D = 6.5A	--	0.43	0.54	Ω
g _{FS}	Forward Transconductance	V _{DS} = 40V, I _D = 6.5A (Note 4)	--	15	--	S
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz	--	1580	2055	pF
C _{oss}	Output Capacitance		--	180	235	pF
C _{rss}	Reverse Transfer Capacitance		--	20	25	pF
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{DD} = 250V, I _D = 13A R _G = 25Ω (Note 4, 5)	--	25	60	ns
t _r	Turn-On Rise Time		--	100	210	ns
t _{d(off)}	Turn-Off Delay Time		--	130	270	ns
t _f	Turn-Off Fall Time		--	100	210	ns
Q _g	Total Gate Charge	V _{DS} = 400V, I _D = 13A V _{GS} = 10V (Note 4, 5)	--	43	56	nC
Q _{gs}	Gate-Source Charge		--	7.5	--	nC
Q _{gd}	Gate-Drain Charge		--	18.5	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain-Source Diode Forward Current		--	--	13	A
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	52	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0V, I _S = 13A	--	--	1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0V, I _S = 13A	--	100	160	ns
Q _{rr}	Reverse Recovery Charge	di _F /dt = 100A/μs (Note 4)	--	0.35	--	μC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. L = 5.6mH, I_{AS} = 13A, V_{DD} = 50V, R_G = 25 Ω, Starting T_J = 25°C
3. I_{SD} ≤ 13A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C
4. Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 2%
5. Essentially Independent of Operating Temperature Typical Characteristics